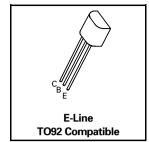
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ZTX450 ZTX451

ISSUE 2 – MARCH 1994

FEATURES

- * 60 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot}= 1 Watt



ABSOLUTE MAXIMUM RATINGS.

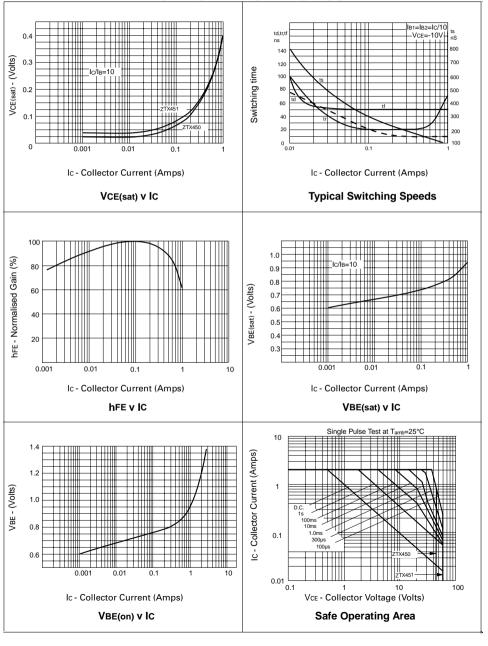
PARAMETER	SYMBOL	ZTX450	ZTX451	UNIT
Collector-Base Voltage	V_{CBO}	60	80	٧
Collector-Emitter Voltage	V_{CEO}	45	60	٧
Emitter-Base Voltage	V_{EBO}	5		٧
Peak Pulse Current	I _{CM}	2		Α
Continuous Collector Current	I _C		Α	
Power Dissipation at T _{amb} =25°C	P _{tot}		W	
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

· and										
PARAMETER	SYMBOL	ZT	X450	ZTX451		UNIT	CONDITIONS.			
		MIN.	MAX.	MIN.	MAX.					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60		80		V	I _C =100μA			
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	45		60		V	I _C =10mA*			
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5		5		V	$I_E=100\mu A$			
Collector Cut-Off Current	I _{CBO}		0.1		0.1	μ Α μ Α	V _{CB} =45V V _{CB} =60V			
Emitter Cut-Off Current	I _{EBO}		0.1		0.1	μА	V _{EB} =4V			
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.25		0.35	V	I _C =150mA, I _B =15mA*			
Base-Emitter Saturation Voltage	V _{BE(sat)}		1.1		1.1	V	I _C =150mA, I _B =15mA*			
Static Forward Current Transfer Ratio	h _{FE}	100 15	300	50 10	150		I _C =150mA, V _{CE} =10V* I _C =1A, V _{CE} =10V*			
Transition Frequency	f _T	150		150		MHz	I _C =50mA, V _{CE} =10V f=100MHz			
Output Capacitance	C _{obo}		15		15	pF	V _{CB} =10V, f=1MHz			

ZTX450 ZTX451





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